

UNISONIC TECHNOLOGIES CO., LTD

7N60K-MTQ **Power MOSFET**

6.2A, 600V N-CHANNEL POWER MOSFET

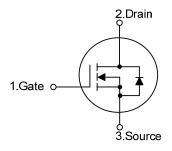
DESCRIPTION

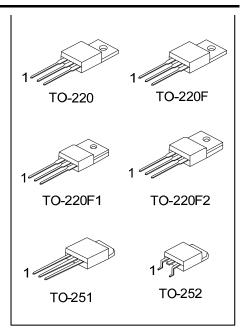
The UTC 7N60K-MTQ is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in switching power supplies and adaptors.

FEATURES

- * $R_{DS(ON)}$ < 1.4 Ω @ V_{GS} = 10V, I_{D} = 3.5A
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

SYMBOL

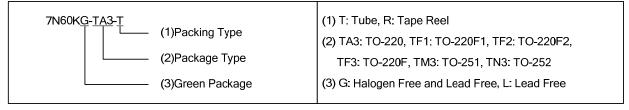




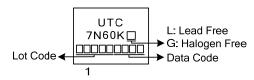
ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1 2 3		Packing		
7N60KL-TA3-T	7N60KG-TA3-T	TO-220	G	D	S	Tube	
7N60KL-TF1-T	7N60KG-TF1-T	TO-220F1	G	D	S	Tube	
7N60KL-TF2-T	7N60KG-TF2-T	TO-220F2	G	D	S	Tube	
7N60KL-TF3-T	7N60KG-TF3-T	TO-220F	G	D	S	Tube	
7N60KL-TM3-T	7N60KG-TM3-T	TO-251	G	D	S	Tube	
7N60KL-TN3-R	7N60KG-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



MARKING



www.unisonic.com.tw 1 of 6

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V _{GSS}	±30	V
Avalanche Current (Note 2)		I _{AR}	7	Α
Continuous Drain Current		I _D	7	Α
Pulsed Drain Current (Note 2)		I_{DM}	28	Α
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	340	mJ
	Repetitive (Note 2)	E _{AR}	13	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.8	ns
Power Dissipation	TO-220		142	W
	TO-220F/TO-220F1 TO-220F2	P_D	48	W
	TO-251/TO-252		59	W
Junction Temperature		TJ	+150	°C
Operating Temperature		T_OPR	-55 ~ + 150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3. L = 18.33mH, I_{AS} = 7A, V_{DD} = 90V, R_{G} = 25 Ω , Starting T_{J} = 25°C
- 4. $I_{SD} \le 7A$, di/dt $\le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25^{\circ}C$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2	$ heta_{JA}$	62.5	°C/W
	TO-251/TO-252		110	°C/W
Junction to Case	TO-220		0.88	°C/W
	TO-220F/TO-220F1 TO-220F2	θ_{JC}	2.6	°C/W
	TO-251/TO-252		2.1	°C/W

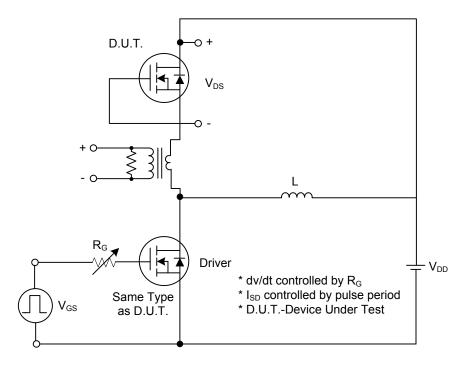
■ ELECTRICAL CHARACTERISTICS (T」=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS					•		
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	600			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =600V, V _{GS} =0V			10	μA
			V _{DS} =480V, V _{GS} =0V, T _J =125°C			10	μA
Gate- Source Leakage Current	rward		$V_{G}=30V$, $V_{DS}=0V$			100	nA
	everse	- I _{GSS}	V _{GS} =-30V, V _{DS} =0V			-100	nA
Breakdown Voltage Temperature		$\triangle BV_{DSS}/\triangle T_{J}$	L 050A D-f		0.50		1//00
Coefficient			I _D =250μA, Referenced to 25°C		0.53		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage	Gate Threshold Voltage		$V_{DS}=V_{GS}$, $I_{D}=250\mu A$			4.0	V
Static Drain-Source On-State Resi	stance	V _{GS(TH)} R _{DS(ON)}	V_{GS} =10V, I_{D} =3.5A			1.4	Ω
DYNAMIC CHARACTERISTICS							-
Input Capacitance		C _{ISS}			740	1110	pF
Output Capacitance		Coss	V _{DS} =25V, V _{GS} =0V, f=1.0 MHz		140	210	pF
Reverse Transfer Capacitance	Reverse Transfer Capacitance				8	12	pF
SWITCHING CHARACTERISTICS	3	C _{RSS}					-
Total Gate Charge		Q_{G}	\/ _F0\/ _4.24 \/ _40\/		68	82	nC
Gate-Source Charge		Q_{GS}	V _{DS} =50V, I _D =1.3A, V _{GS} =10V I _G =100μA (Note 1, 2)		6		nC
Gate-Drain Charge		Q_GD	I _G -100μΑ (Note 1, 2)		6.6		nC
Turn-On Delay Time		t _{D(ON)}			60	72	ns
Turn-On Rise Time		t _R	V_{DD} =30V, I_{D} =0.5A, R_{G} =25 Ω		66	79	ns
Turn-Off Delay Time			(Note 1, 2)		120	144	ns
Turn-Off Fall Time		t _{D(OFF)}	1		64	77	ns
DRAIN-SOURCE DIODE CHARA	CTERIST	ICS AND MAX	IMUM RATINGS		_		
Maximum Continuous Drain-Source	e Diode					7	Δ.
Forward Current		Is				7	Α
Maximum Pulsed Drain-Source Di	sed Drain-Source Diode					28	Α
Forward Current		I _{SM}				20	А
Drain-Source Diode Forward Voltage		V_{SD}	I _S =7A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time		t _{rr}	I _{SD} =7A, dI _S /dt=100A/μs		368		ns
Body Diode Reverse Recovery Charge		Q _{rr}			3.5		nC

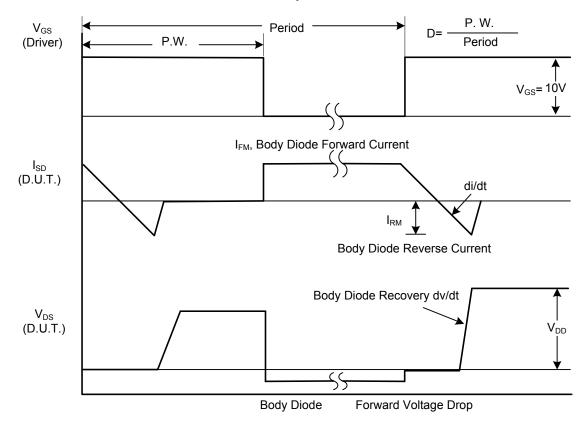
Notes: 1. Pulse Test: Pulse width \leq 300 μ s, Duty cycle \leq 2%.

^{2.} Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS



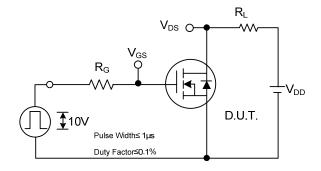
Peak Diode Recovery dv/dt Test Circuit

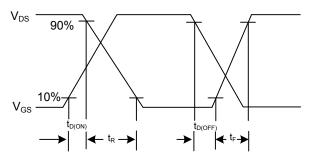


Peak Diode Recovery dv/dt Waveforms

7N60K-MTQ Power MOSFET

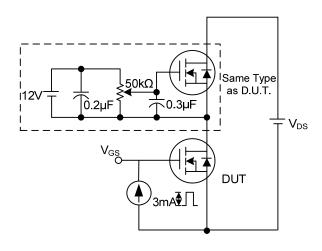
■ TEST CIRCUITS AND WAVEFORMS (Cont.)

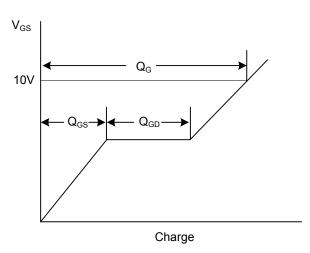




Switching Test Circuit

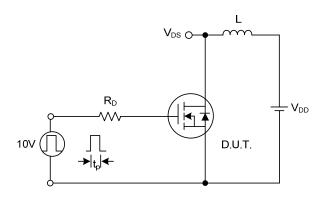
Switching Waveforms

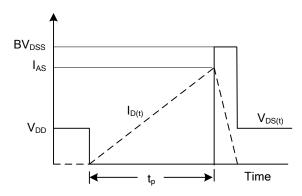




Gate Charge Test Circuit

Gate Charge Waveform



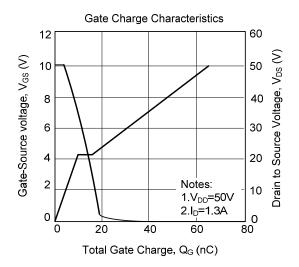


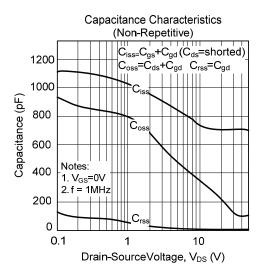
Unclamped Inductive Switching Test Circuit

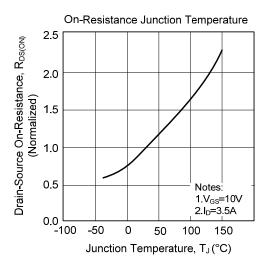
Unclamped Inductive Switching Waveforms

7N60K-MTQ Power MOSFET

■ TYPICAL CHARACTERISTICS







UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.